SD106WS

Schottky Barrier Diode

VOLTAGE RANGE: 30V PEAK PULSE POWER:250mW

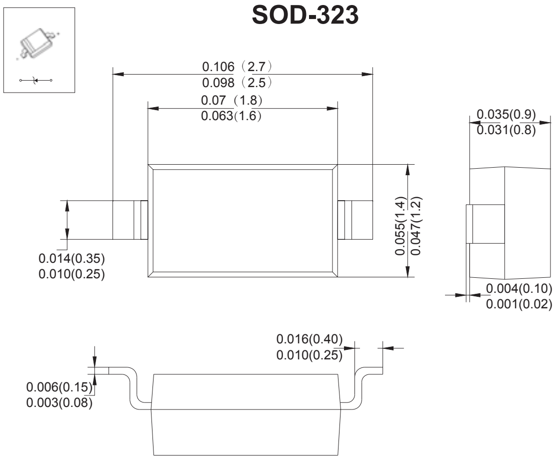
FEATURES

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge
- Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications

MECHANICAL DATA

- ●Case: SOD-323 Small Outline Plastic Package
- ●Polarity: Color band denotes cathode end
- ●Mounting Position: Any

SOD-323



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-repetitive peak reverse voltage	V_{RM}	30	V
Forward current	I_{FM}	200	mA
Non-repetitive Forward Surge Current @t=8.3ms	I_{FSM}	1	A
Power dissipation	P_{tot}	250	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	400	℃/W
Junction temperature	T_J	125	℃
Storage temperature	T_{STG}	-55~+150	℃

Electrical Specification (T_A=25@25°C unless otherwise specified)

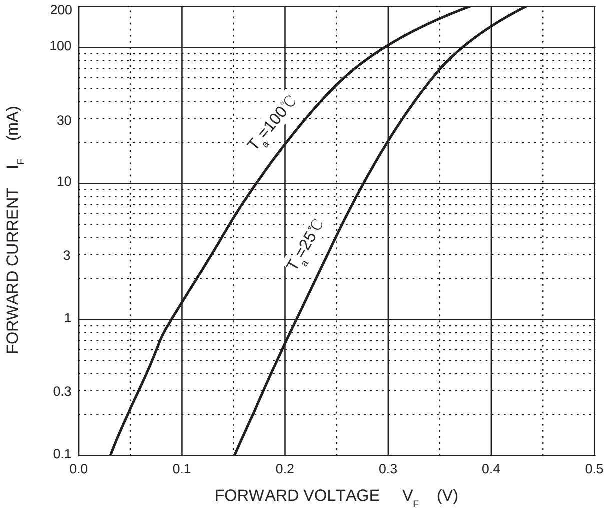
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	30			V	I_R=100uA
Forward voltage	V_F		260 320 420 490	550	mV	I_F=2mA I_F=15mA I_F=100mA I_F=200mA
Reverse current	I_R			5	μA	V_R=30V
Capacitance between terminals	C_T			15	pF	V_R=10V,f=1MHz

MARKING: S21

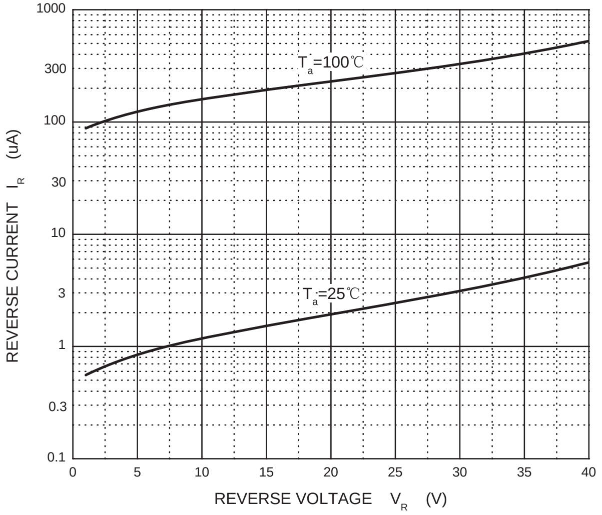
RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

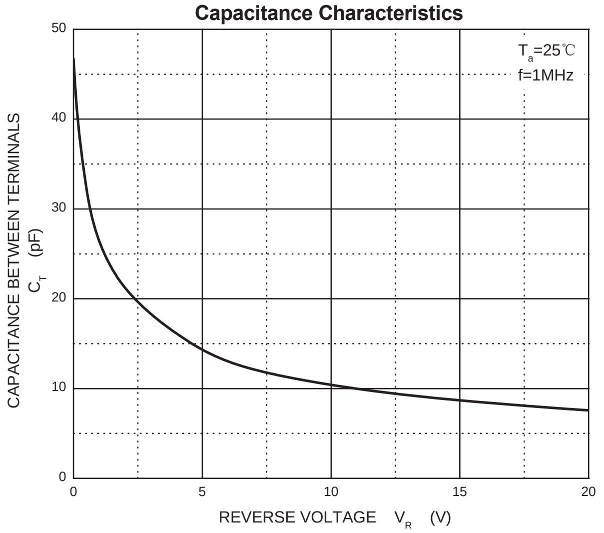
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve